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2004 04 08(21) 10-2001-0022625
(22) 2001 04 26(65)
(43)10-2001-0098900
2001 11 08

(30) 2000-128356 2000 04 27 (JP)

(73) 가 가 1 1 1

(72) 1-9-2가 가

(74)

:

(54)

, 1 , 1 ,
(contact hole),
.

1

1
2 1
3 1
4 1
5 1
6 1
7

< >

10 --- (1), 12 --- (2),
 14 --- , 16 --- ,
 17 --- , 18 --- ,
 20 --- , 22 --- ,
 23 --- , 24 --- ,
 25 --- , 26 --- ,
 27 --- , 28 --- ,
 30 --- , 32 --- ,
 34 --- , 35 --- ,
 36 --- , 37 --- ,
 38 --- , 39 --- (),
 40 --- (), 41 --- (2),
 42 --- (), 44 --- (),
 46 --- , 47 --- ,
 50 --- .

act hole) , (被覆) (cont
 , , , (高
 精細) 가 . 2 (glass)
 , 1 ,
 , , 2 3 (color
 filter) , , 2 (spacer
)
 , , 가 . 가 , (凹)
 가 가 가 .
 가 .
 , 가 ,
 ,
 , 1 , 1 , ,
 , , ,
 , , 1 2 ,
 1 , ,
 , ,

(rubbing)

가 , 가 , 가

()

$\frac{1}{1}$ 1 2 1

(23)

(14) (50) 1 (10) , 2 (12)

(23) , 1 (10) (27)

(41) (12) (38)

(23)

(10) (SiOx) (under coat) (16)

(16) , (MoW) (18) (20) (18)

) , 2 (17) (17) (a-Si) (22)

(18) (20) (SiNx) (24)

(24) , / (Al/Mo) (26) (26)

(25) (25)

(positive stagger type) (27)가 (27)

(27) (28) (30)

(30) 1 (32)

(30) , ITO(Indium Tin Oxide) (34) (20)

(32)

(34) (36) (32)

(36) (47)가

(41) (12) (35) , (35)

(41) , 2 (37) , (37)

(35) (38)

ITO (39, 40) (

(23) (41) (39, 40)

42, 44) (23) (41) 가 (14)

(23) (41)

3 6

(1) 3 (10) (16) CVD

(18) (16) (sputtering) MoW

(20) (17) (a-Si)

CVD

(22) , CVD (24)

(26) (25) Al/Mo

(P) (22) (22) n⁺-a-Si

(28)

(2) , CVD (30)

(, 4 (30) (34)

()

ITO(Indium Tin Oxide) (32) (34) (20) (32) (

).

(32) (23) (spin coat) (46) (

(3) , 5 (前期)). (34) (46) (充填) (36) (32)

(4) , 6 (後期)). (47) (47) (46)

(47) , (34) (46) 가 (47) (36) .

(34) (46) 가 (34) (46) 가 (滴下) , 가 ,

(34) (46) 가 (浸漬) 7 (34) (46) 가 (46) A

(34) B (34) 6.5 μ m 5.5 μ m . A, B 가

(34) (46) (46) 가 (34) C (46) (34) D (72) (46) 60) (46)

(5) , (34) (36) (41) [(39, 40)] (14) ,

(42, 44) (50) (23) (41) (14) (封入)

$\frac{2}{2}$ 1 (1) (36) , (1 , (34)

).

(2) , (23) (1 ,).

, 1 2 1 (41) (35)가 ,

(23) (30) (35) .

(1) (spinner) , 90 10 (10 μ m) (34) (20

μ m \times 20 μ m) , 200mJ/cm² , 200 60 (燒成)

, 1wt% 가 , , 가 1.5 μ m (35) (

).

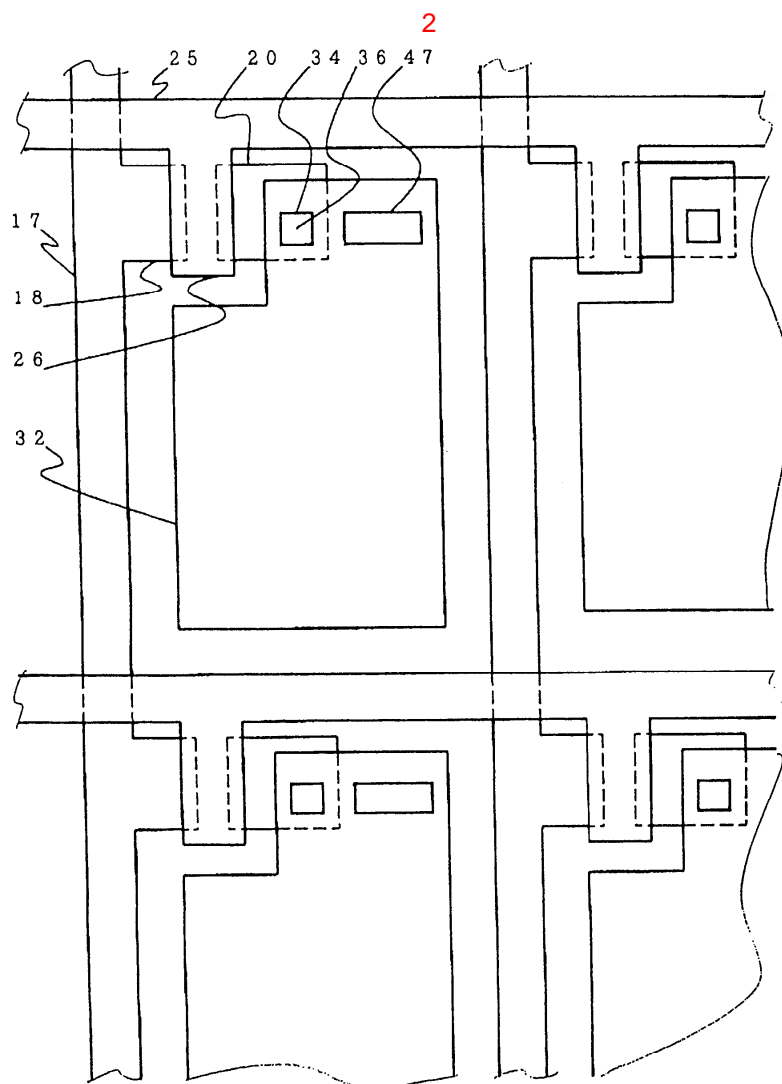
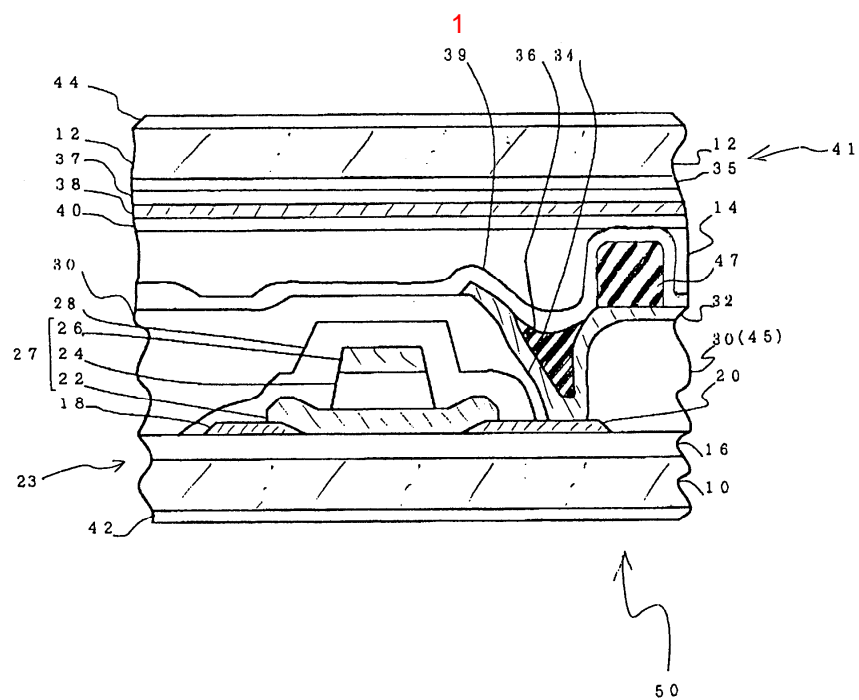
, ITO 0.1 μ m (32) ((34) (18)

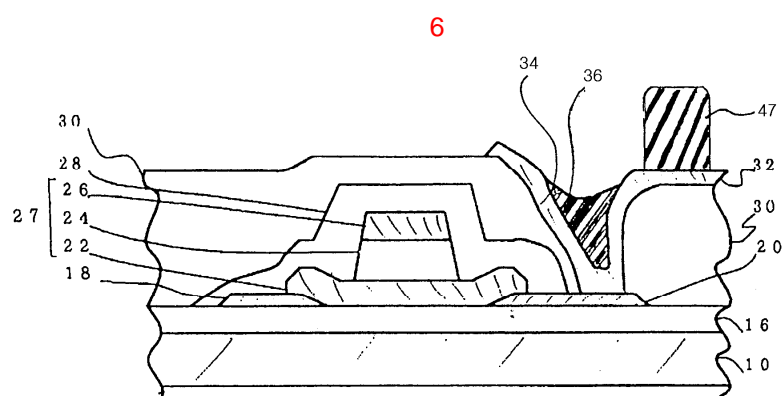
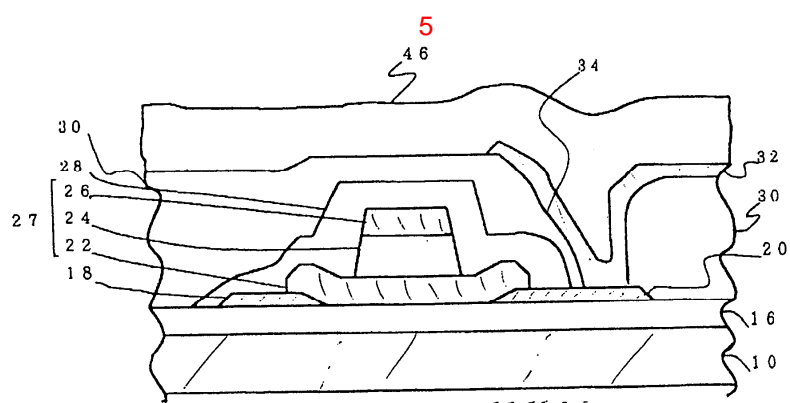
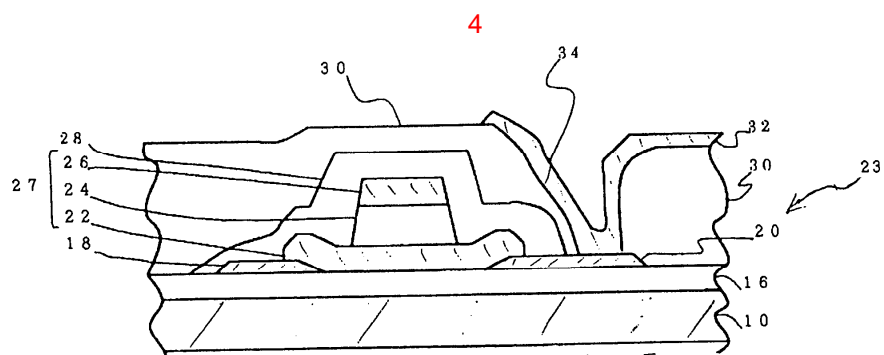
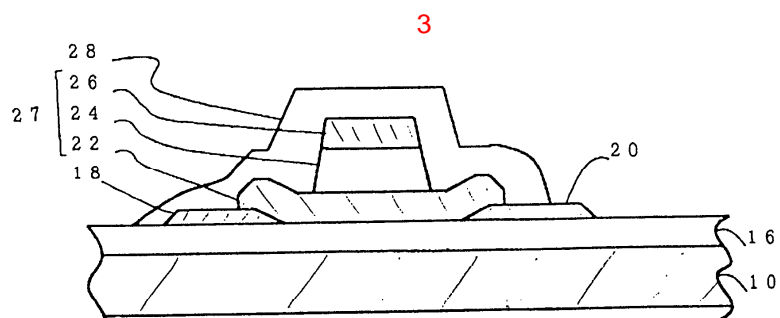
(2) , (47)가 (7 μ m \times 15 μ m) , 90 10 (3 μ m) (34) (20 μ m \times 20 μ m)

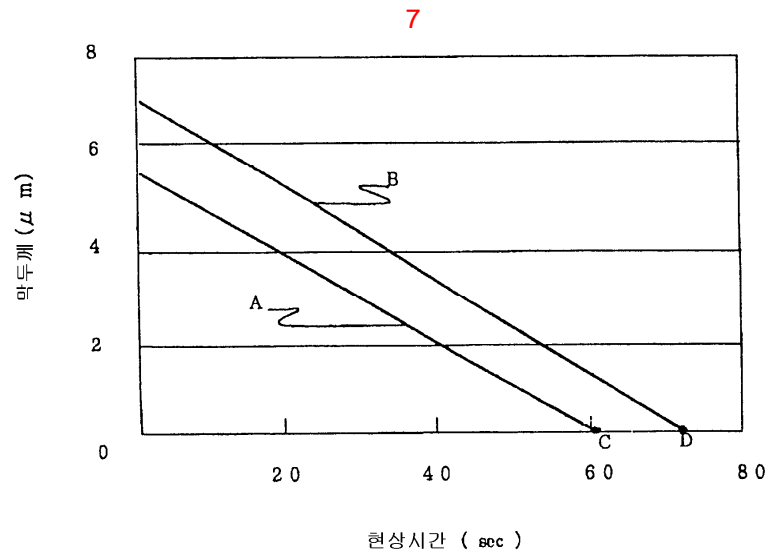
, 300mJ/cm² , pH=11.5 , 200 60 (47) (36) (

).

(3) (38) (23) (41) 가 (39) (40) , (rubbi
ng) . , , ,
 , (23) (41) ,
 , (23) (41) (42, 44)
 , 가
 , 가
 (1) , 2
(2) ,
(3) ,
 2가 ,
 가 ()
 ,
 ,
 , 가
 , 가
 가







专利名称(译)	液晶显示装置和液晶显示装置的制造方法		
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外部链接	Espacenet		

摘要(译)

该液晶显示器包括：中继形成在第一基板上的接触孔的阵列面板；以及开关元件，在该第一基板上形成涂覆该开关元件并形成的层间绝缘膜，以及层间绝缘膜层间绝缘膜形成在该层间绝缘膜上，并且配备有连接到开关元件的像素电极，以及下面形成的取向层的间隔物，涂覆该像素电极并形成该取向层。形成为与间隔物相同的材料的平坦化层布置在对应于接触孔的区域内的像素电极层和取向层之间。

